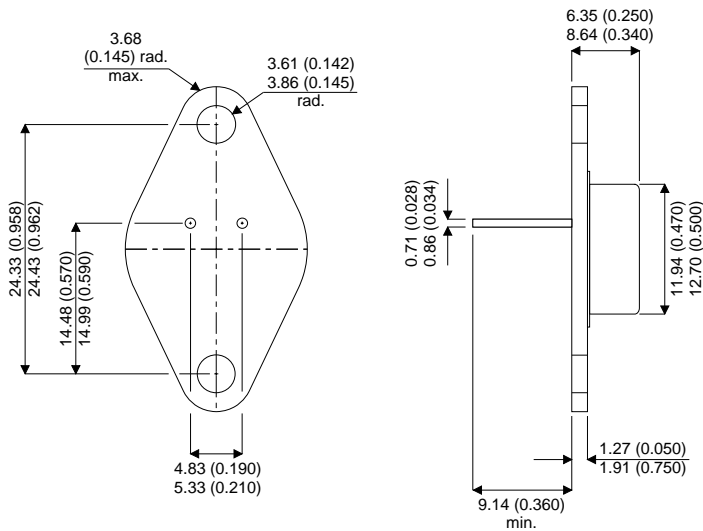


**MECHANICAL DATA**

Dimensions in mm



**TO66 Package.**

Pin 1 – Base      Pin 2 – Emitter      Case - Collector

**PNP  
SILICON TRANSISTOR,  
EPITAXIAL BASE**

**FEATURES:**

- LF Large Signal Power Amplification
- Medium Current Switching

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{CBO}$	Collector – Base Voltage (Open Emitter)	- 90V
$V_{CEO}$	Collector – Emitter Voltage (Open Base)	- 55V
$V_{CER}$	Collector – Emitter Voltage $R_{BE} = 100\Omega$	- 60V
$V_{CEX}$	Collector – Base Voltage $V_{BE} = +1.5V$	- 90V
$V_{EBO}$	Emitter – Base Voltage	-7V
$I_C$	Collector Current	-4V
$I_B$	Base Current	-2V
$P_{tot}$	Power Dissipation	29W
$T_J$	Maximum Junction Temperature	200°C
$T_{STG}$	Storage Temperature	-65 to 200°C
$R_{th-(j-c)}$	Junction to Case.	6°C / W

**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CEX}$ Collector Emitter Cut Off Current	$V_{CE} = -90V$ $V_{BE} = +1.5V$			-1	mA
	$V_{CE} = -30V$ $V_{BE} = +1.5V$ $T_{case} = 150^{\circ}C$			-5	
$V_{CEO(SUS)}$ * Collector Emitter Breakdown Voltage	$I_C = -100mA$ $I_B = 0$	-55			V
$V_{CER(SUS)}$ * Collector Emitter Breakdown Voltage	$I_C = -100mA$ $R_{BE} = 100\Omega$	-60			
$V_{(BR)EBO}$ * Emitter Base Breakdown Voltage	$I_E = -1A$ $I_C = 0$	-7			V
$h_{21E}$ * Static Forward Current Transfer Ratio	$V_{CE} = -4V$ $I_C = -0.5A$	25		250	—
$V_{CE(sat)}$ * Collector Emitter Saturation Voltage	$I_C = -0.5A$ $I_B = -0.05A$			-1	V
$V_{BE}$ * Base Emitter Voltage	$V_{CE} = -4V$ $I_C = -0.5A$			-1.7	V
$f_T$ Transition Frequency	$V_{CB} = -10V$ $I_C = -0.2A$ $f = 1MHz$	4			MHz

\* Pulse test  $t_p = 300\mu s$ ,  $\delta < 2\%$